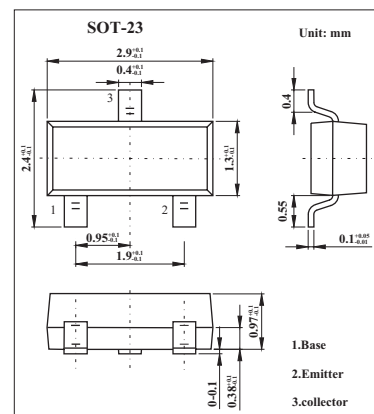


Silicon Transistor

2SA1226

■ Features

- High gain bandwidth product
- Low output capacitance
- Low noise



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (RBE = ∞)	V _{CB0}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EB0}	-5.0	V
Collector current - continuous	I _C	-30	mA
Total power dissipation at 25°C ambient temperature	P _T	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -40V, I _E = 0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -4.0V, I _C = 0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -10V, I _C = -1.0mA	40	90	180	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1.0mA		-0.09	-0.3	V
Base-emitter voltage	V _{BE}	V _{CE} = -10V, I _C = -10mA	-0.67	-0.72		V
Gain bandwidth product	f _T	V _{CE} = -10V, I _E = 1.0mA	250	400		MHz
Output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1.0MHz		1.1	2.0	pF
Noise figure	NF	V _{CE} = -10V, I _C = -1.0mA, R _G = 500Ω, f = 1.0MHz		3.5		dB

■ hFE Classification

Marking	E2	E3	E4
hFE	40~80	60~120	90~180